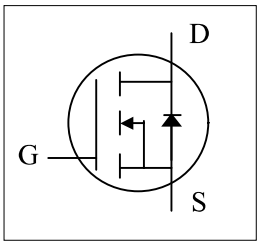
N-Channel Power MOSFET

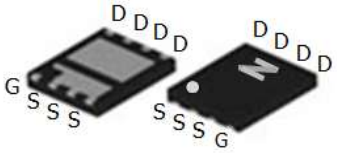
- ▼ **Capable of 2.5V Gate Drive**
- ▼ **Small Size & Ultra_Low $R_{DS(ON)}$**
- ▼ **RoHS Compliant & Halogen-Free**



BV_{DSS}	20V
$R_{DS(ON)}$	8.5mΩ
I_D[3]	30A

Description

AP2080Q series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



DFN3 x 3

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Drain Current, V_{GS} @ 4.5V[3]	30	A
I_D@T_A=70℃	Drain Current, V_{GS} @ 4.5V[3]	19	A
I_{DM}	Pulsed Drain Current[1]	70	A
P_D@T_A=25℃	Total Power Dissipation	24	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	5	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	26	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V, I_D=20A	-	8.5	9.8	mΩ
		V_{GS}=2.5V, I_D=12A	-	-	14	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=1mA	0.6	-	0.9	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=20A	-	130	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=16V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=20A	-	62	99.2	nC
Q_{gs}	Gate-Source Charge	V_{DS}=10V	-	4	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	21	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V	-	12	-	ns
t_r	Rise Time	I_D=1A	-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	100	-	ns
t_f	Fall Time	V_{GS}=5V	-	80	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	4000	6400	pF
C_{oss}	Output Capacitance	V_{DS}=10V	-	780	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	625	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.4	2.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=2.5A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=20A, V_{GS}=0V,	-	43	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	26	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 2oz copper pad of FR4 board, t ≤10sec; 135°C/W when mounted on min. copper pad.

4.Maximum current limited by package.

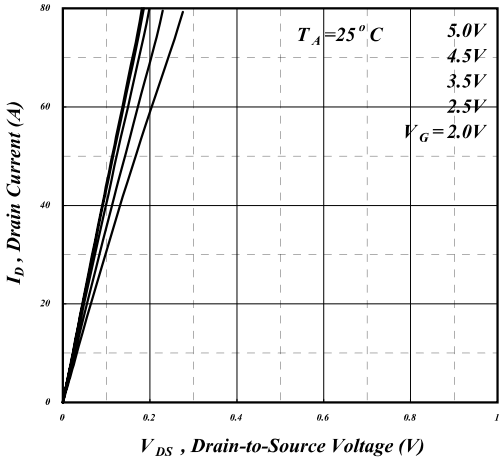


Fig 1. Typical Output Characteristics

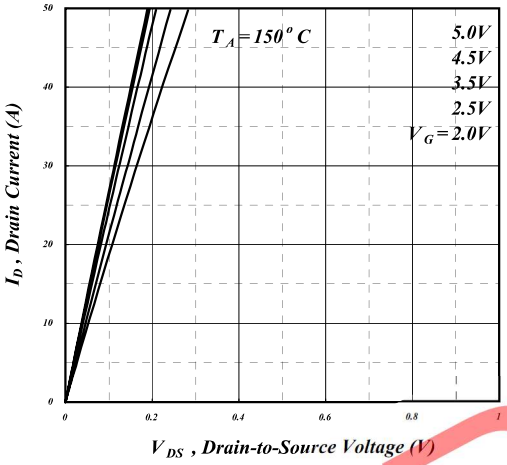


Fig 2. Typical Output Characteristics

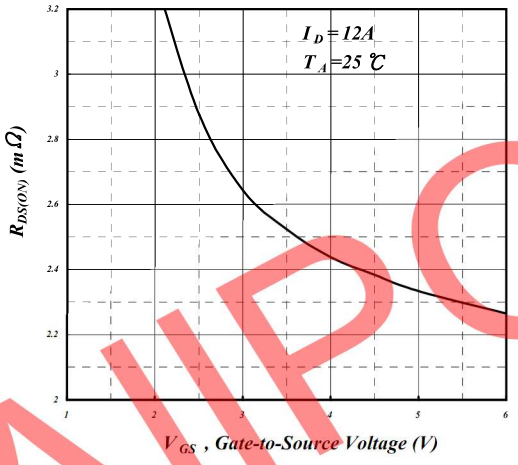


Fig 3. On-Resistance v.s. Gate Voltage

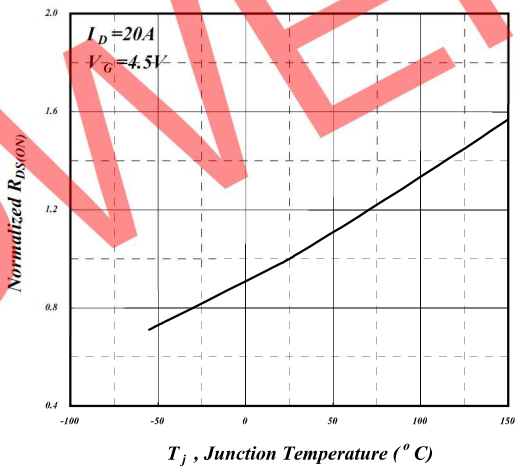


Fig 4. Normalized On-Resistance v.s. Junction Temperature

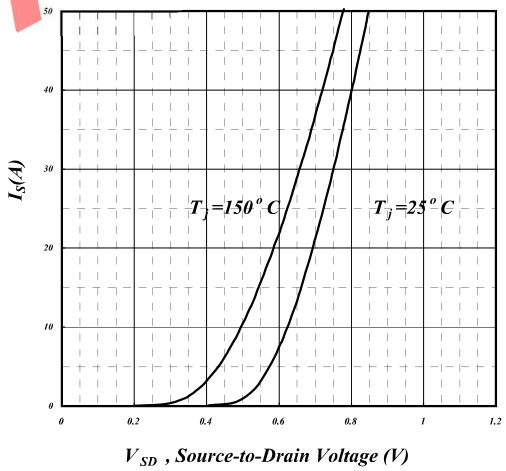


Fig 5. Forward Characteristic of Reverse Diode

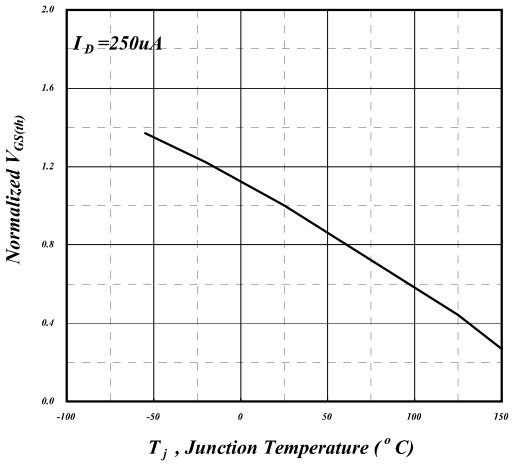


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

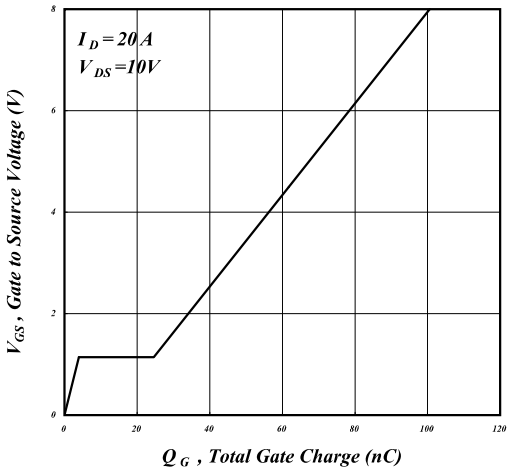


Fig 7. Gate Charge Characteristics

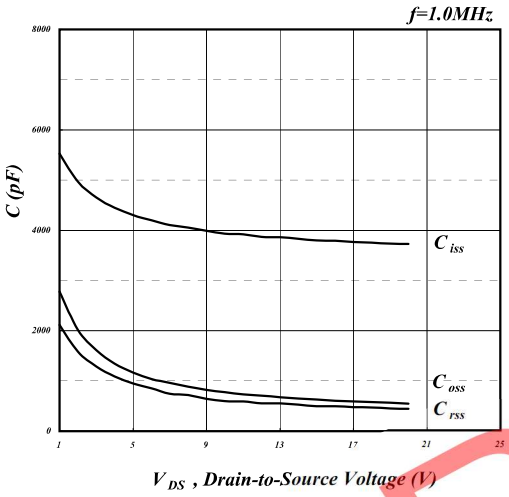


Fig 8. Typical Capacitance Characteristics

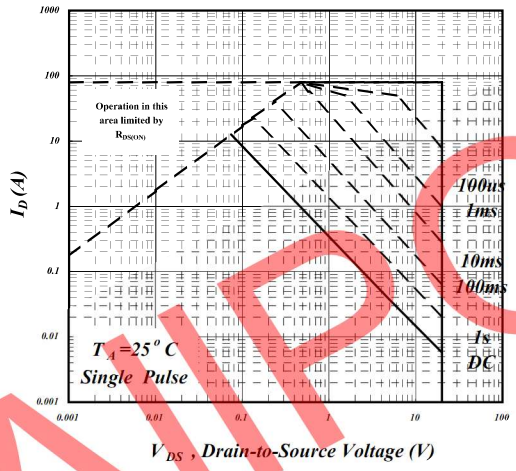


Fig 9. Maximum Safe Operating Area

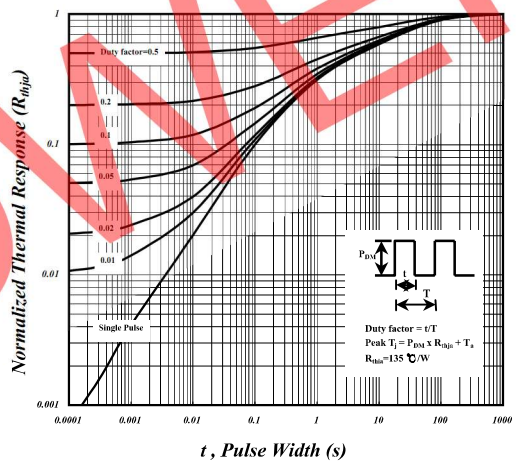


Fig 10. Effective Transient Thermal Impedance

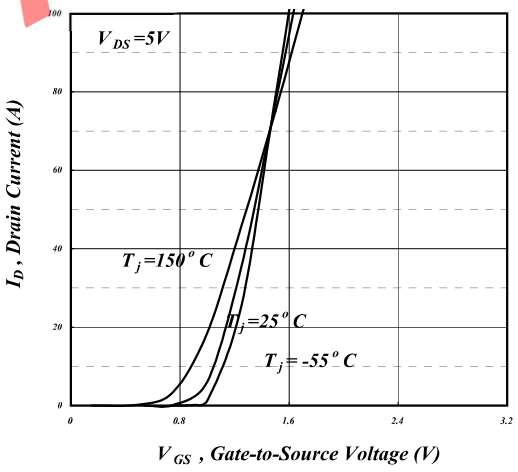


Fig 11. Transfer Characteristics

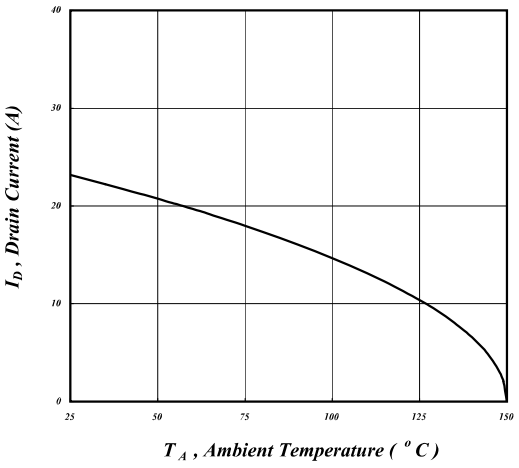


Fig 12. Drain Current v.s. Ambient Temperature

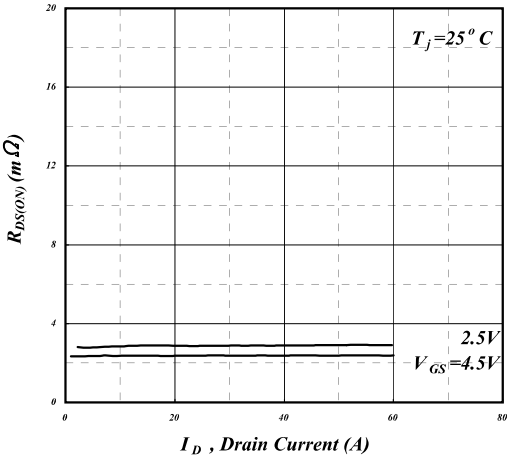


Fig 13. Typ. Drain-Source on State Resistance

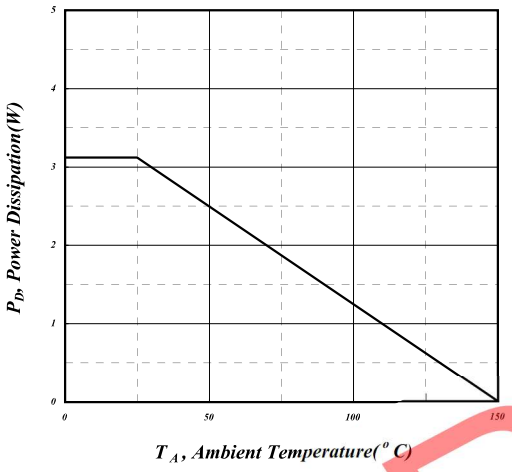
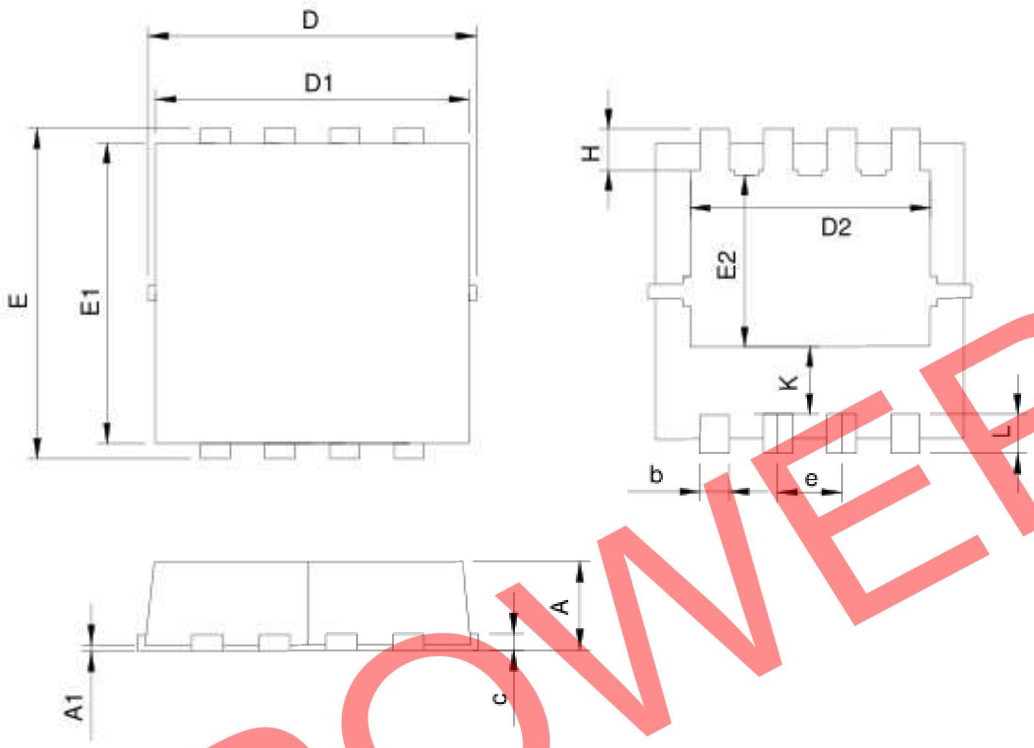


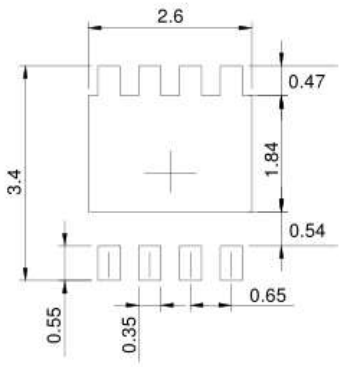
Fig 14. Total Power Dissipation

●**Dimensions(DFN3×3)**



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm